

Features

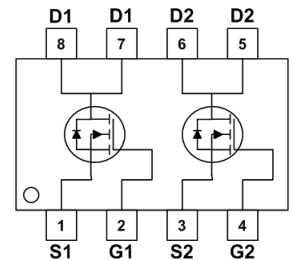
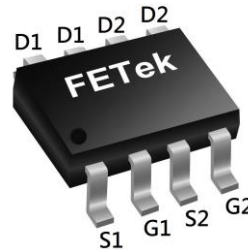
- Advanced Trench MOS Technology
- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available

Product Summary


BVDSS	RDSON	ID
100V	68mΩ	4A

Application

- Portable Equipment.
- Battery Powered Systems.
- Hard Switching and High-Speed Circuit.

SOP8 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	4	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	3	A
I_{DM}	Pulsed Drain Current ²	25	A
EAS	Single Pulse Avalanche Energy ³	0.8	mJ
I_{AS}	Avalanche Current	4	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	85	$^\circ\text{C/W}$
	Thermal Resistance Junction-ambient ¹ ($t \leq 10\text{S}$)	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	40	$^\circ\text{C/W}$

**Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=4A$	---	---	68	m Ω
		$V_{GS}=4.5V, I_D=3A$	---	---	94	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.5	---	2.9	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	10	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=4A$	---	14	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	3	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=50V, V_{GS}=10V, I_D=4A$	---	11.9	---	nC
Q_{gs}	Gate-Source Charge		---	2.6	---	
Q_{gd}	Gate-Drain Charge		---	1.7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, R_G=3\Omega, I_D=4A$	---	3.8	---	ns
T_r	Rise Time		---	25.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	16	---	
T_f	Fall Time		---	8.8	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	620	---	pF
C_{oss}	Output Capacitance		---	105	---	
C_{riss}	Reverse Transfer Capacitance		---	63	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	4	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=4A, di/dt=100A/\mu s$,	---	30	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	37	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=4A$
- 4.The power dissipation is limited by 150 $^\circ\text{C}$ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

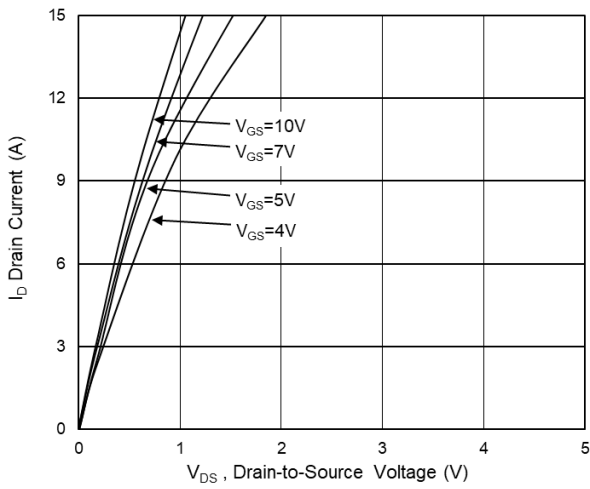


Fig.1 Typical Output Characteristics

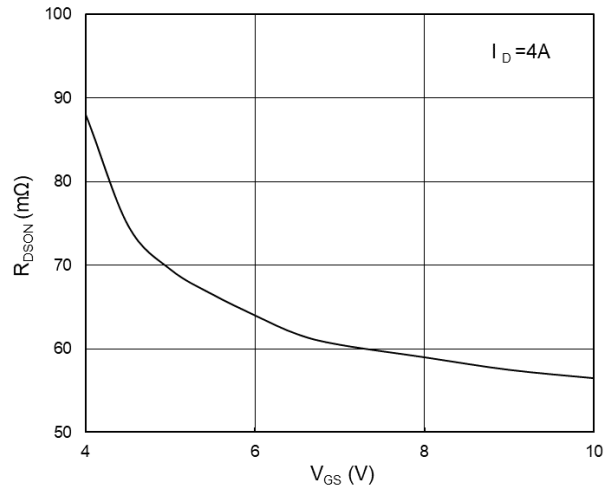


Fig.2 On-Resistance vs G-S Voltage

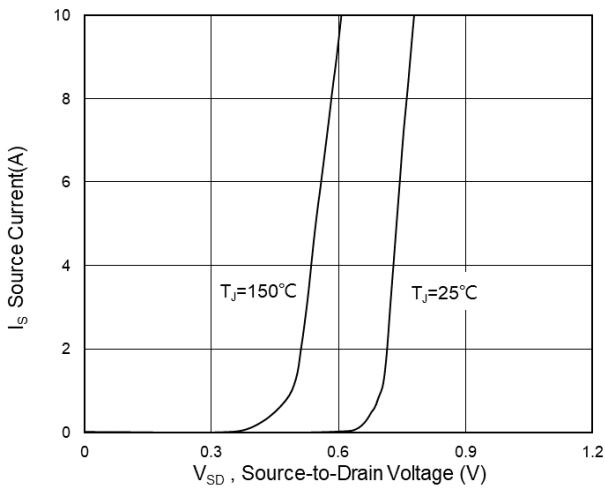


Fig.3 Source Drain Forward Characteristics

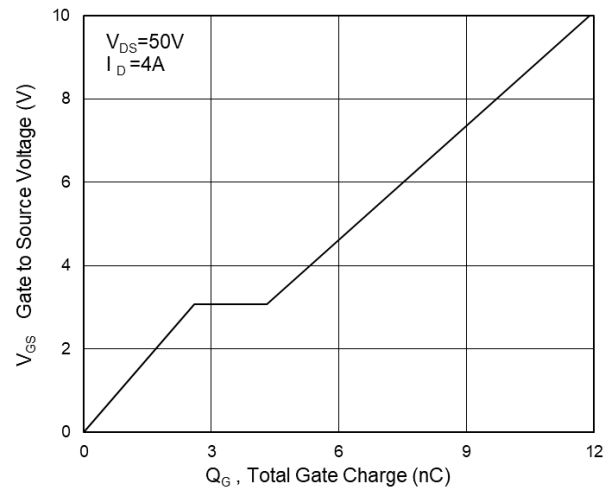


Fig.4 Gate-Charge Characteristics

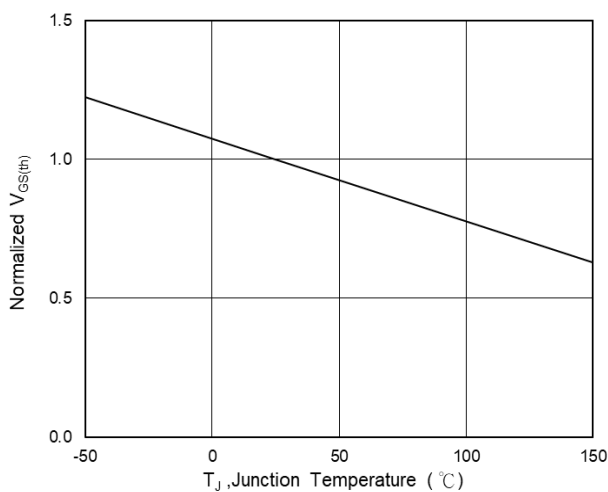


Fig.5 Normalized $V_{GS(th)}$ vs T_J

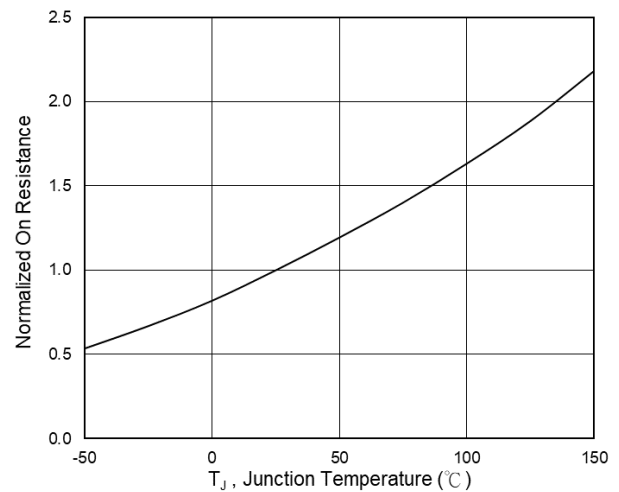


Fig.6 Normalized $R_{DS(on)}$ vs T_J

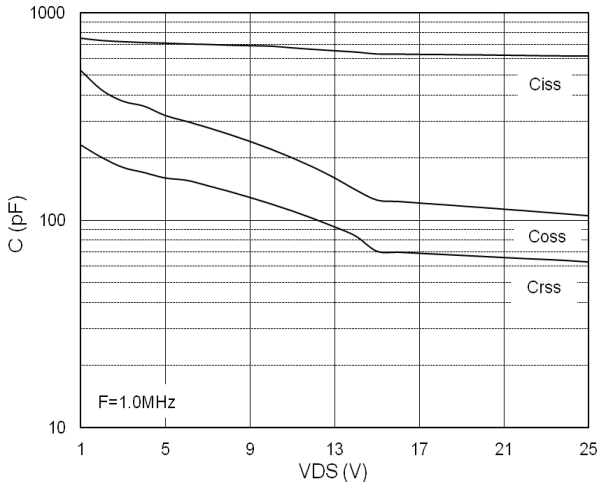


Fig.7 Capacitance

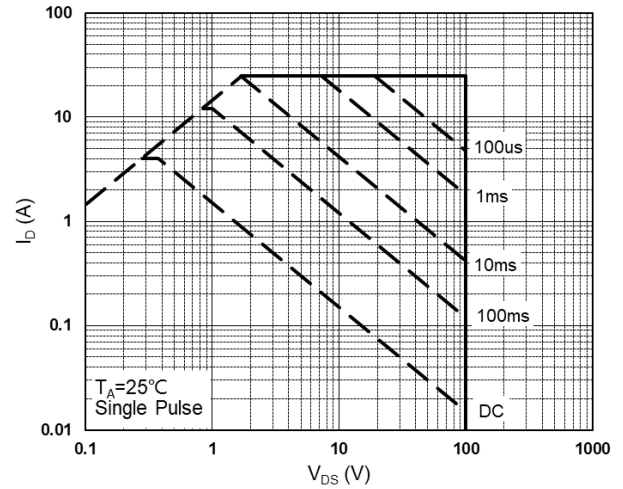


Fig.8 Safe Operating Area

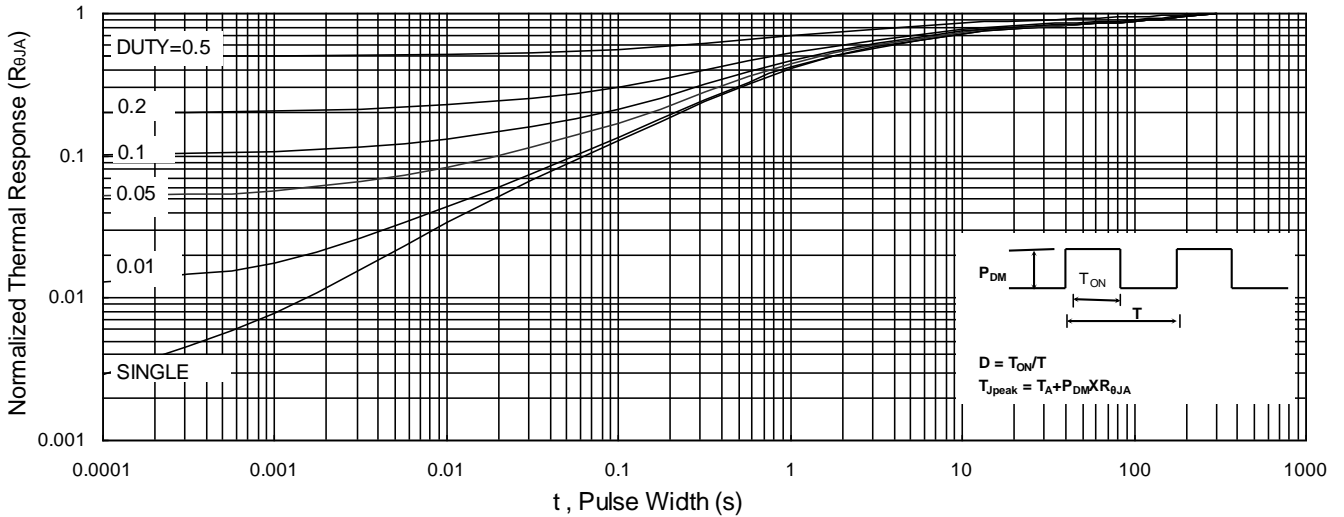


Fig.9 Normalized Maximum Transient Thermal Impedance

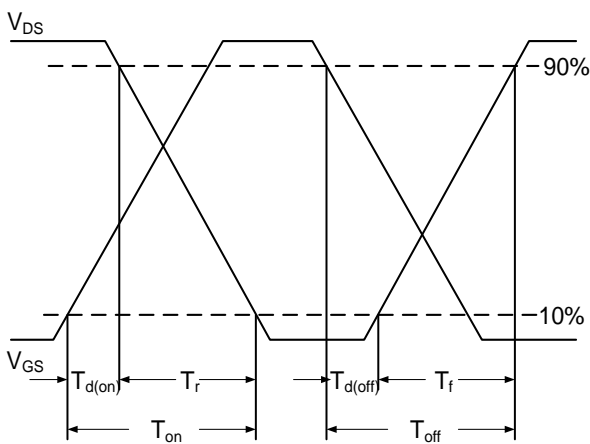


Fig.10 Switching Time Waveform

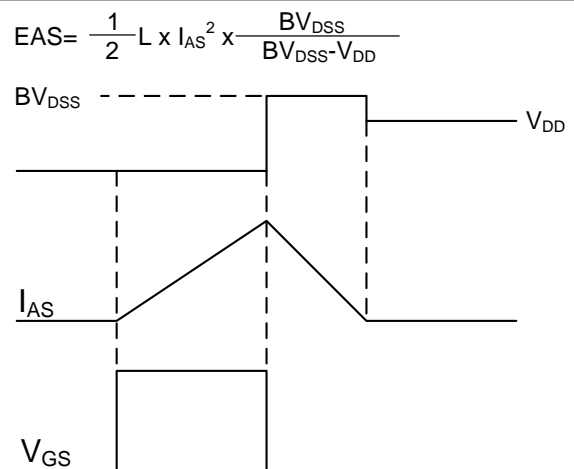


Fig.11 Unclamped Inductive Waveform